

HiPerFRED²

DPG10I200PM

V_{RRM}	=	200 V
I _{FAV}	=	10 A
t _{rr}	=	35 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

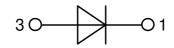
Part number

DPG10I200PM



Backside: isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

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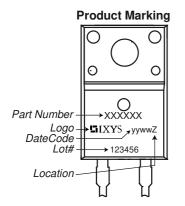
Fast Diode					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			200	V	
V _{RRM}	max. repetitive reverse blocking ve	oltage	$T_{VJ} = 25^{\circ}C$			200	V	
I _R	reverse current, drain current	V_{R} = 200 V	$T_{vJ} = 25^{\circ}C$			1	μA	
		V_{R} = 200 V	$T_{vJ} = 150^{\circ}C$			0.06	mA	
V _F	forward voltage drop	I _F = 10 A	$T_{VJ} = 25^{\circ}C$			1.27	V	
		I _F = 20 A				1.45	V	
		$I_{\rm F} = 10 {\rm A}$	T _{vJ} = 150°C			0.98	V	
		$I_{F} = 20 \text{ A}$				1.17	V	
FAV	average forward current	T _c = 125°C	$T_{vJ} = 175^{\circ}C$			10	А	
		rectangular d = 0.5						
V _{F0}	threshold voltage		$T_{vJ} = 175^{\circ}C$			0.74	V	
r _F	slope resistance	ss calculation only				17.7	mΩ	
\mathbf{R}_{thJC}	thermal resistance junction to case	9				4.4	K/W	
R _{thCH}	thermal resistance case to heatsin	k			0.5		K/W	
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			35	W	
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_{R} = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			140	А	
C	junction capacitance	$V_{\rm R}$ = 150 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		15		pF	
I _{RM}	max. reverse recovery current		$T_{vJ} = 25 °C$		3		А	
		$I_{\rm F} = 10 \text{A}; V_{\rm R} = 130 \text{V}$	T _{vJ} = 125 °C		5.5		Α	
t _{rr}	reverse recovery time	I _F = 10 A; V _R = 130 V -di _F /dt = 200 A/μs	$T_{VJ} = 25 \circ C$		35		ns	
	ر 	1	$T_{vJ} = 125 ^{\circ}C$		45		ns	

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DPG10I200PM

Package TO-220FP					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					35	Α
T _{vj}	virtual junction temperature				-55		175	°C
T _{op}	operation temperature				-55		150	°C
T _{stg}	storage temperature				-55		150	°C
Weight						2		g
M _D	mounting torque				0.4		0.6	Nm
F _c	mounting force with clip				20		60	Ν
d _{Spp/App}	creepage distance on surface s	triking distance through air	terminal to terminal	3.2	2.7			mm
d _{Spb/Apb}	creepage distance on surface (s	tinking distance through an	terminal to backside	2.5	2.5			mm
V	isolation voltage	t = 1 second	50/60 Hz, RMS; IIso∟ ≤ 1 mA		2500			V
		t = 1 minute			2100			V



Part description

- D = Diode P = HiPerFRED
- G = extreme fast 10 = Current Rating [A]
- I = Single Diode 200 = Reverse Voltage [V] PM = TO-220ACFP (2)

	Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
[Standard	DPG10I200PM	DPG10I200PM	Tube	50	503771

Similar Part	Package	Voltage class
DPG10I200PA	TO-220AC (2)	200

Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 175^{\circ}C$
)[R]-	Fast Diode		
V _{0 max}	threshold voltage	0.74		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	14.5		mΩ

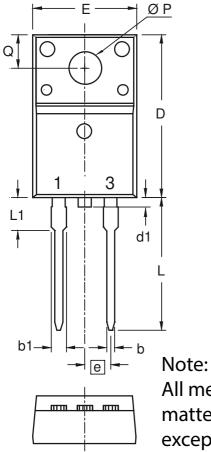
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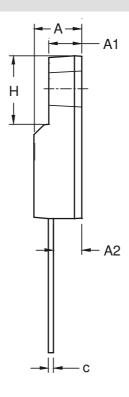
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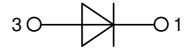
Outlines TO-220FP





All metal surface are matte pure tin plated except trimmed area.

Dim.	Millim	neters	Inc	nes
Dim.	min	max	min	max
Α	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
b1	1.27	1.47	0.050	0.058
С	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
d1	0	1.10	0	0.043
Е	9.96	10.36	0.392	0.408
е	2.54	BSC	0.100	BSC
Н	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
ØΡ	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134



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